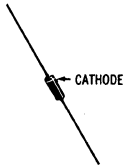


1N3213, 1N3214

For Specifications, See 1N248B Data.

1N3282 thru 1N3286 (SILICON)



CASE 51
(DO-7)

Low-current silicon rectifiers for applications requiring extremely high reverse-voltage capability. Hermetically sealed, subminiature glass package, offering excellent stability and reliability under environmental extremes.

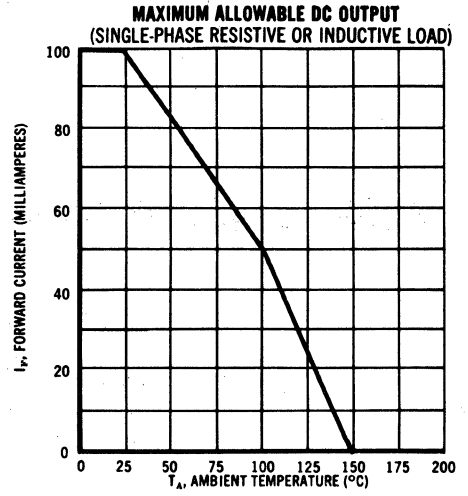
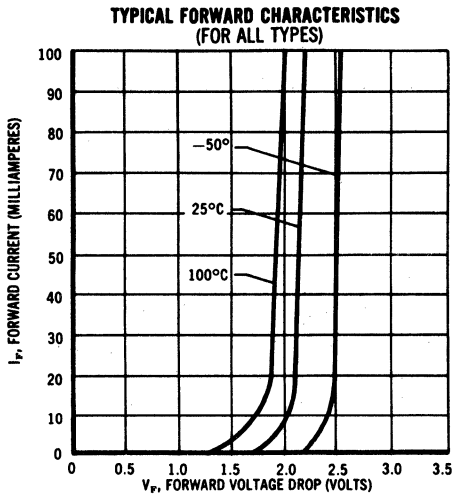
MAXIMUM RATINGS (At 60 cps Sinusoidal Input, Resistive or Inductive Load)

Rating	Symbol	1N3282	1N3283	1N3284	1N3285	1N3286	Unit	
Peak Repetitive Reverse Voltage	$V_{RM(rep)}$	1000	1500	2000	2500	3000	Volts	
DC Blocking Voltage	V_R							
RMS Reverse Voltage	V_r	700	1050	1400	1750	2100	Volts	
Average Half-Wave Rectified Forward Current (25°C Ambient) (100°C Ambient)	I_O	100 50	100 50	100 50	100 50	100 50	mA mA	
Peak Surge Current (1/2-cycle, 60 Hz)	$I_{FM(surge)}$	2.5	2.5	2.5	2.5	2.5	Amp	
Peak Repetitive Forward Current	$I_{FM(rep)}$	0.50	0.50	0.50	0.50	0.50	Amp	
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to + 150						°C

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Forward Voltage Drop @ 100 mA, Continuous DC (25°C)	V_F	2.5	Volts
Maximum Full-Cycle Average Forward Voltage Drop @ Rated Current (100°C)	$V_{F(AV)}$	1.2	Volts
Maximum Reverse Current @ Rated DC Voltage (25°C) (100°C)	I_R	1.0 10.0	μA
Maximum Full-Cycle Average Reverse Current @ Max Rated PIV and Current (as Half-Wave Rectifier, Resistive Load, 100°C)	$I_{R(AV)}$	10.0	μA
Typical Thermal Resistance, Junction to Ambient	θ_{JA}	400	°C/W

1N3282 thru 1N3286 (continued)



1N3305 thru 1N3350

For Specifications, see 1N2804 Data.